

## S1AB THRU S1MB

### 1.0A SURFACE MOUNT GLASS PASSIVATED RECTIFIER



#### Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop
- Low Power Loss
- Built-in Strain Relief
- Plastic Case Material has UL Flammability Classification Rating 94V-0
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

#### Circuit Diagram



#### Mechanical Data

- Case: SMB molded plastic body
- Terminals: Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 0.09 grams

#### Maximum Ratings and Electrical Characteristics @T<sub>A</sub>=25°C unless otherwise specified

Type Number	Symbol	S1AB	S1BB	S1DB	S1GB	S1JB	S1KB	S1MB	Units
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	50	100	200	400	600	800	1000	V
Working Peak Reverse Voltage	V <sub>RWM</sub>								
DC Blocking Voltage	V <sub>R</sub>								
Maximum RMS voltage	V <sub>RMS</sub>	35	70	140	280	420	560	700	V
Average Rectified Output Current @T <sub>L</sub> = 100°C	I <sub>O</sub>	1.0							A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	30							A
Forward Voltage @ I <sub>F</sub> = 1.0 A	V <sub>F</sub>	1.10							V
Peak Reverse Current @T <sub>A</sub> = 25°C	I <sub>RM</sub>	5.0							μA
At Rated DC Blocking Voltage @T <sub>A</sub> = 125°C		200							
Reverse Recovery Time(Note1)	t <sub>rr</sub>	2.5							μS
Typical Junction Capacitance(Note2)	C <sub>J</sub>	15							pF
Typical Thermal Resistance Junction to Lead (Note 3)	R <sub>θJL</sub>	30							°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +175							°C

Note: 1. Reverse recovery condition I<sub>F</sub>=0.5A, I<sub>R</sub>=1.0A, I<sub>rr</sub>=0.25A  
 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.  
 3. Mounted on P.C.B.with 8.0mm<sup>2</sup> land areas.

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**Ratings and Characteristics Curves**

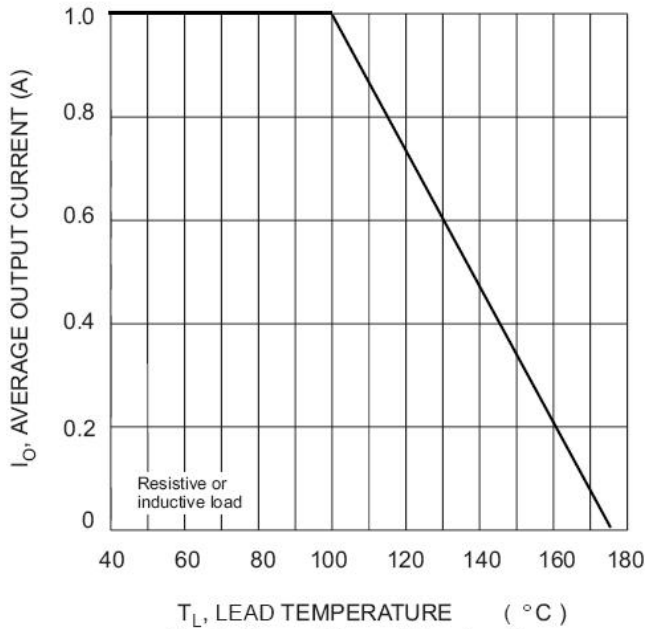


Fig. 1 Forward Current Derating Curve

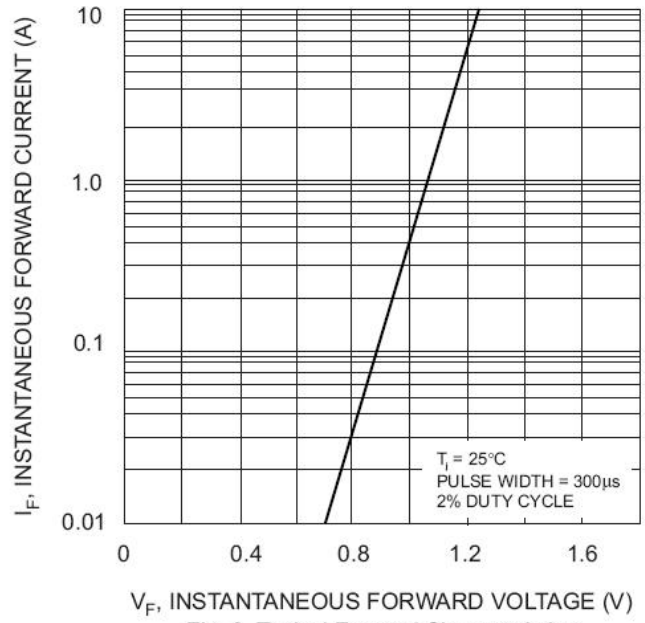


Fig. 2 Typical Forward Characteristics

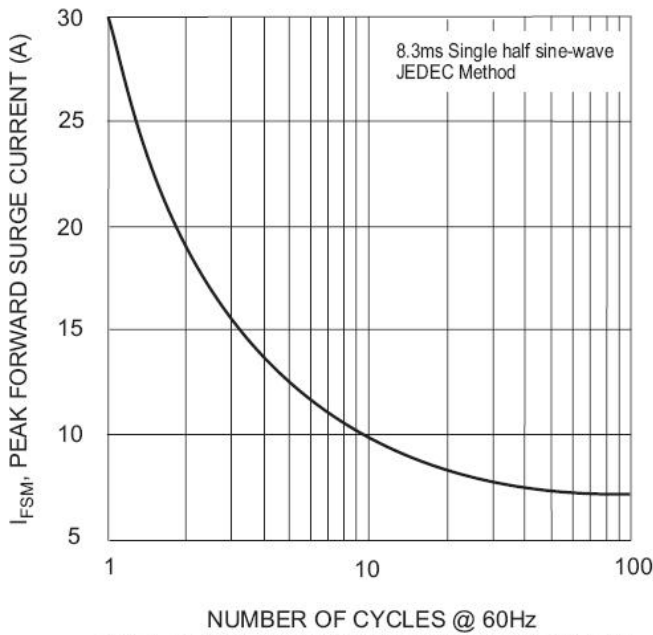


Fig. 3 Max Non-Repetitive Peak Fwd Surge Current

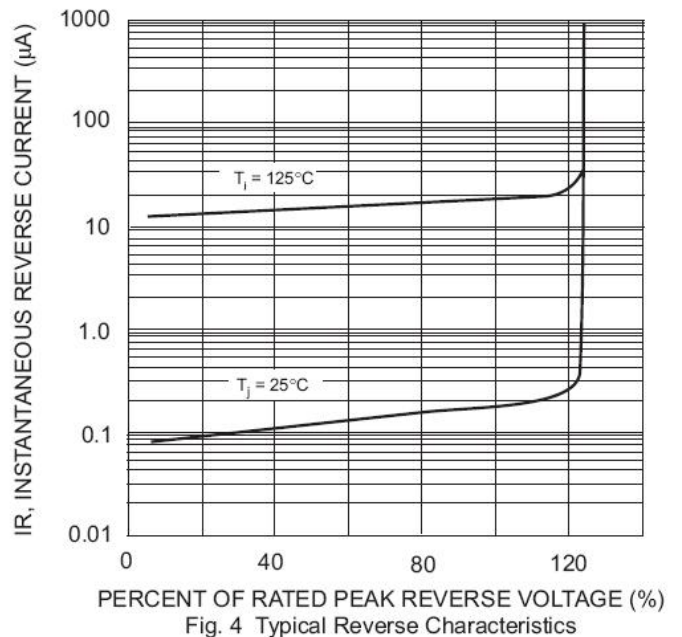
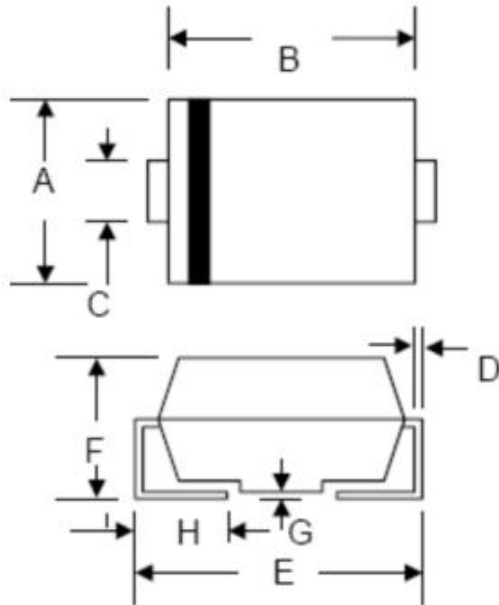


Fig. 4 Typical Reverse Characteristics

### Mechanical Dimensions SMB



SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	3.30	3.94	0.130	0.155
B	4.06	4.70	0.160	0.185
C	1.80	2.20	0.071	0.087
D	0.152	0.305	0.006	0.012
E	4.80	5.59	0.189	0.220
F	2.10	2.60	0.083	0.102
G	0.051	0.203	0.002	0.008
H	0.76	1.52	0.030	0.060

### Ordering Information

Device	Package	Shipping
S1AB-S1MB	SMB(Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

### Marking Diagram

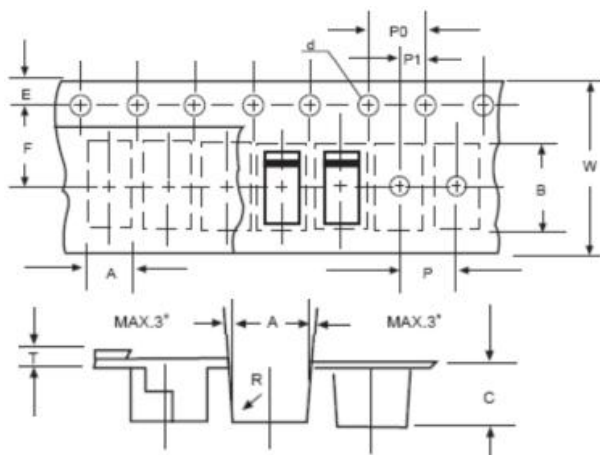


Where XXXXX is YYWWL

S1AB = Type Number  
YY = Year  
WW = Week  
L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

### Carrier Tape Specification SMB



SYMBOL	Millimeters	
	Min.	Max.
A	3.99	4.19
B	5.72	5.92
C	3.23	3.43
d	1.40	1.60
E	1.40	1.60
F	5.60	5.70
P	7.90	8.10
P0	3.90	4.10
P1	1.90	2.10
T	-	0.60
W	11.80	12.20



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